

NTMFS4931N

MOSFET – Power, Single, N-Channel, SO-8 FL 30 V, 246 A

Features

- Low $R_{DS(on)}$ to Improve Conduction and Overall Efficiency
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- OR-ing FET, Power Load Switch, Motor Control
- Refer to Application Note AND8195/D for Mounting Information

End Products

- Motor Control, UPS, Fault-Tolerant Power Systems, Hot Swap

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

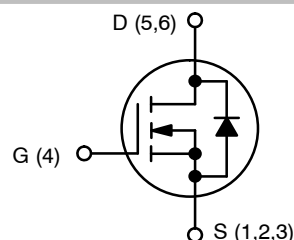
Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	30	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current R _{θJA} (Note 1)	Steady State	T _A = 25°C	I _D	40	A
		T _A = 100°C		25	
Power Dissipation R _{θJA} (Note 1)		T _A = 25°C	P _D	2.74	W
Continuous Drain Current R _{θJA} ≤ 10 s (Note 1)		T _A = 25°C	I _D	77	A
		T _A = 100°C		48	
Power Dissipation R _{θJA} ≤ 10 s (Note 1)		T _A = 25°C	P _D	10.2	W
Continuous Drain Current R _{θJA} (Note 2)		T _A = 25°C	I _D	23	A
		T _A = 100°C		15	
Power Dissipation R _{θJA} (Note 2)		T _A = 25°C	P _D	0.95	W
Continuous Drain Current R _{θJC} (Note 1)		T _C = 25°C	I _D	246	A
		T _C = 100°C		156	
Power Dissipation R _{θJC} (Note 1)		T _C = 25°C	P _D	104	W
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs		I _{DM}	490	A
Operating Junction and Storage Temperature			T _J , T _{STG}	-55 to +150	°C
Source Current (Body Diode)			I _S	100	A
Drain to Source DV/DT			dV/dt	4.4	V/ns



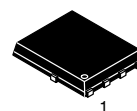
ON Semiconductor®

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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
30 V	1.1 m Ω @ 10 V	246 A
	1.5 m Ω @ 4.5 V	

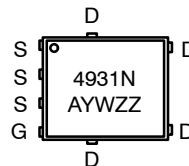


N-CHANNEL MOSFET



**SO-8 FLAT LEAD
CASE 488AA
STYLE 1**

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4931NT1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NTMFS4931NT3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 24\text{ V}$, $V_{GS} = 10\text{ V}$, $I_L = 41\text{ A}_{pk}$, $L = 0.3\text{ mH}$, $R_G = 25\ \Omega$)	E_{AS}	252	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.2	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	45.7	
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	132	
Junction-to-Ambient – ($t \leq 10$ s) (Note 3)	$R_{\theta JA}$	12.3	

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			18		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		15	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.2	1.6	2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			4.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 30\text{ A}$	0.85	1.1	m Ω
			$I_D = 15\text{ A}$	0.82		
		$V_{GS} = 4.5\text{ V}$	$I_D = 30\text{ A}$	1.2	1.5	
			$I_D = 15\text{ A}$	1.2		
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}, I_D = 15\text{ A}$		86		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 15\text{ V}$		9821		pF
Output Capacitance	C_{OSS}			2720		
Reverse Transfer Capacitance	C_{RSS}			234		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		61.5		nC
Threshold Gate Charge	$Q_{G(TH)}$			14.2		
Gate-to-Source Charge	Q_{GS}			25.2		
Gate-to-Drain Charge	Q_{GD}			15.9		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		128		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$		27		ns
Rise Time	t_r			29		
Turn-Off Delay Time	$t_{d(OFF)}$			36		
Fall Time	t_f			24		

5. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$		15		ns
Rise Time	t_r			17		
Turn-Off Delay Time	$t_{d(OFF)}$			80		
Fall Time	t_f			22		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 30 A	T _J = 25°C		0.8	1.0	V
			T _J = 125°C		0.62		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 30 A			64		ns
Charge Time	t _a				33		
Discharge Time	t _b				31		
Reverse Recovery Charge	Q _{RR}				100		nC

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_A = 25^\circ\text{C}$		0.50		nH
Drain Inductance	L_D			0.005		nH
Gate Inductance	L_G			1.84		nH
Gate Resistance	R_G			0.7	1.8	Ω

5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

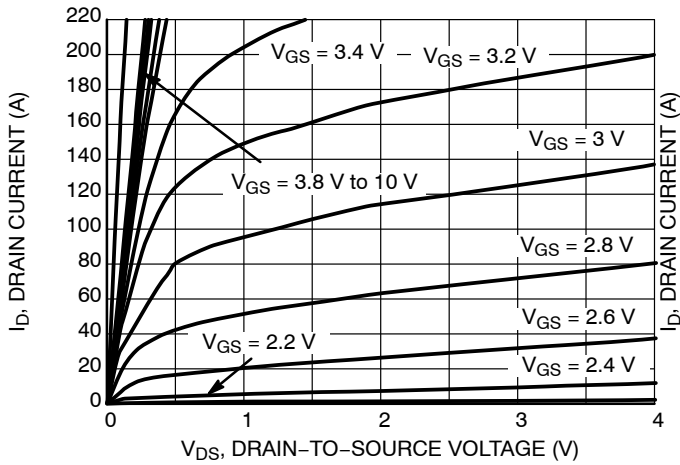


Figure 1. On-Region Characteristics

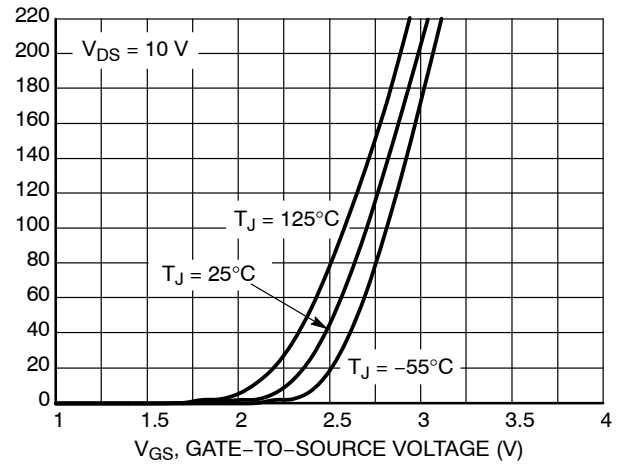


Figure 2. Transfer Characteristics

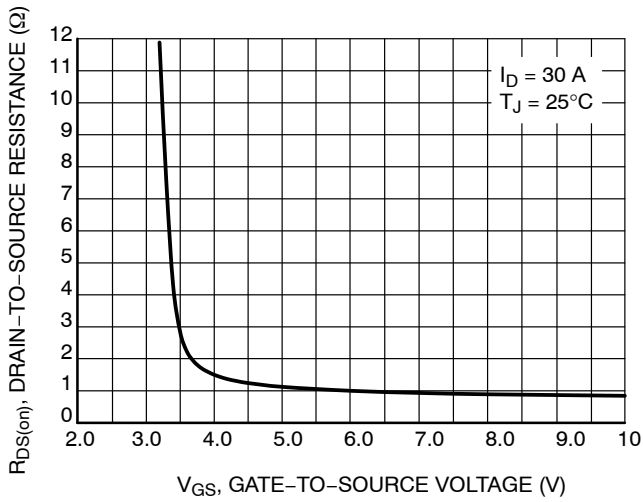


Figure 3. On-Resistance vs. Gate-to-Source Voltage

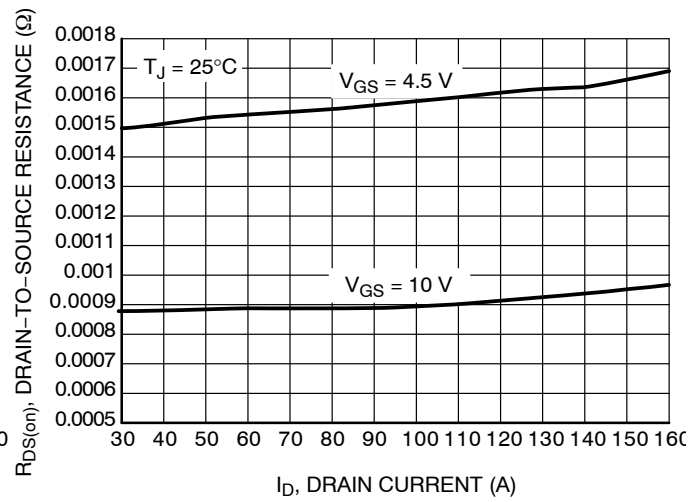


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

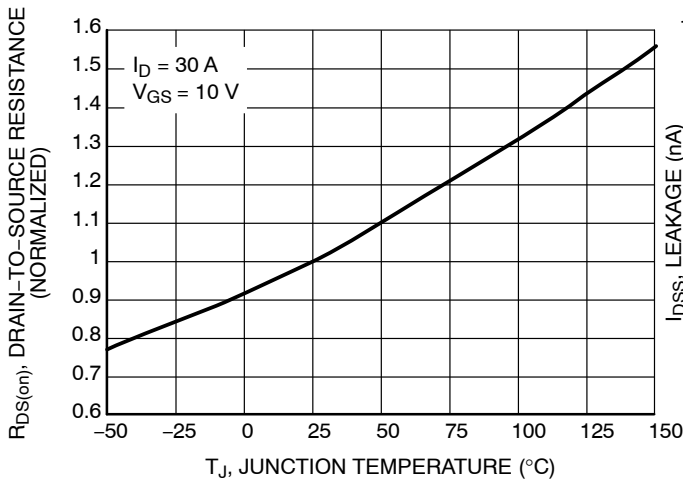


Figure 5. On-Resistance Variation with Temperature

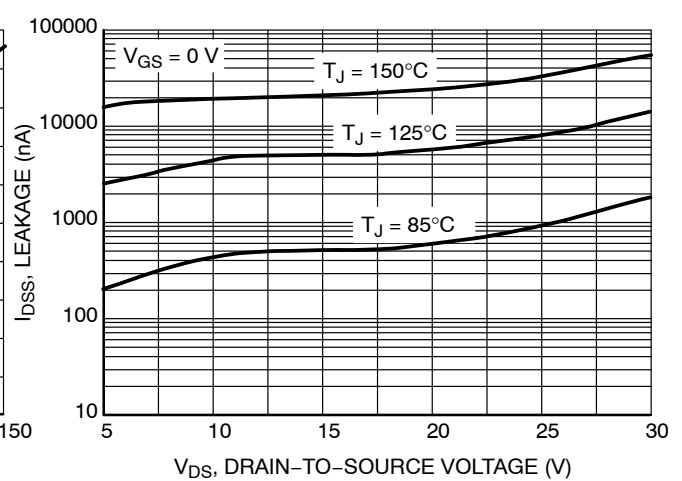


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

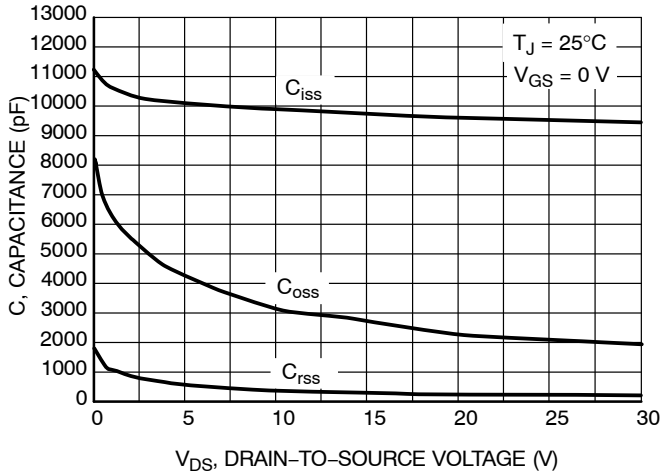


Figure 7. Capacitance Variation

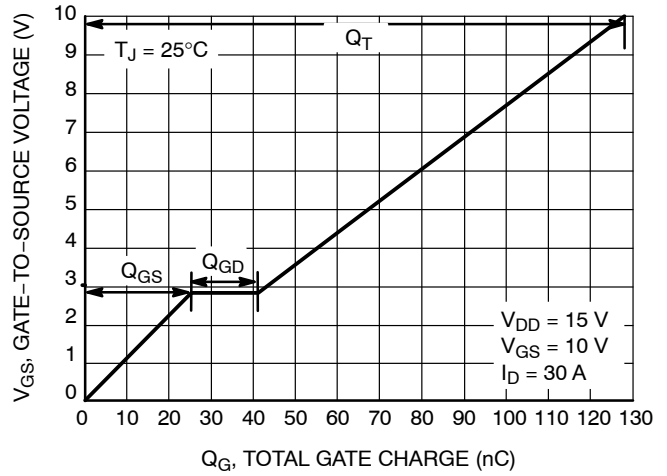


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

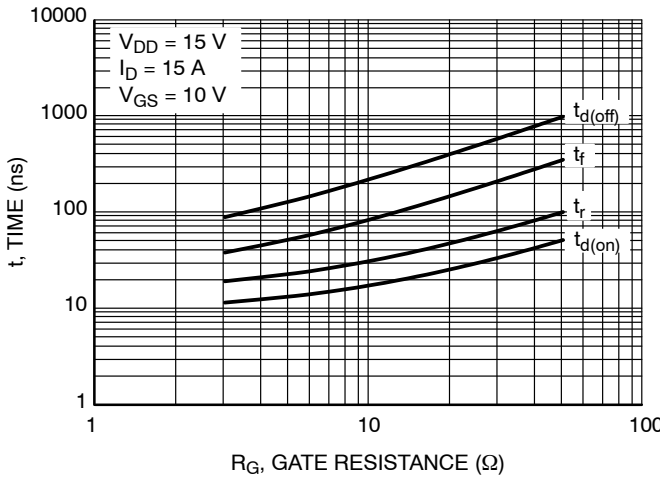


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

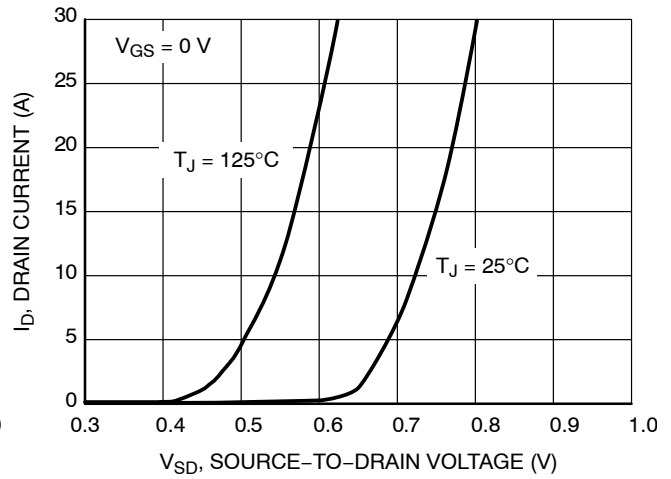


Figure 10. Diode Forward Voltage vs. Current

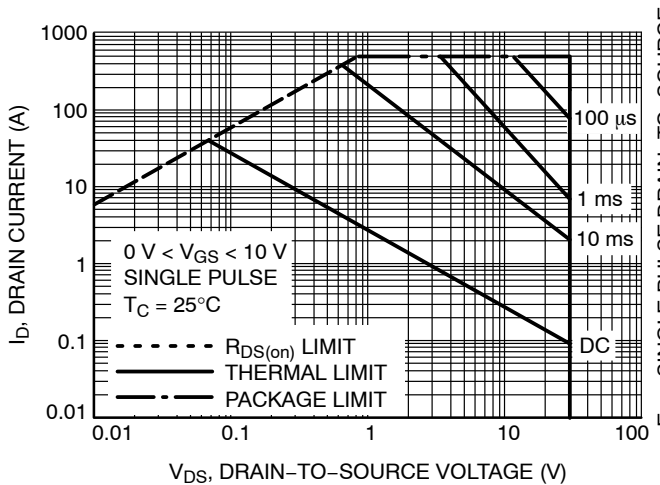


Figure 11. Maximum Rated Forward Biased Safe Operating Area

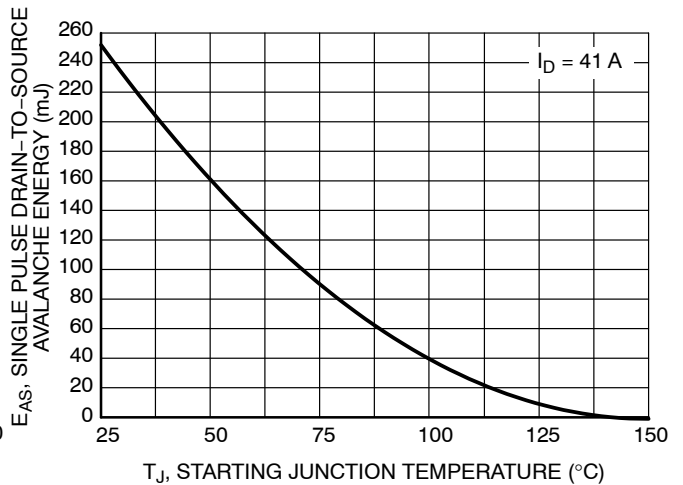


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL CHARACTERISTICS

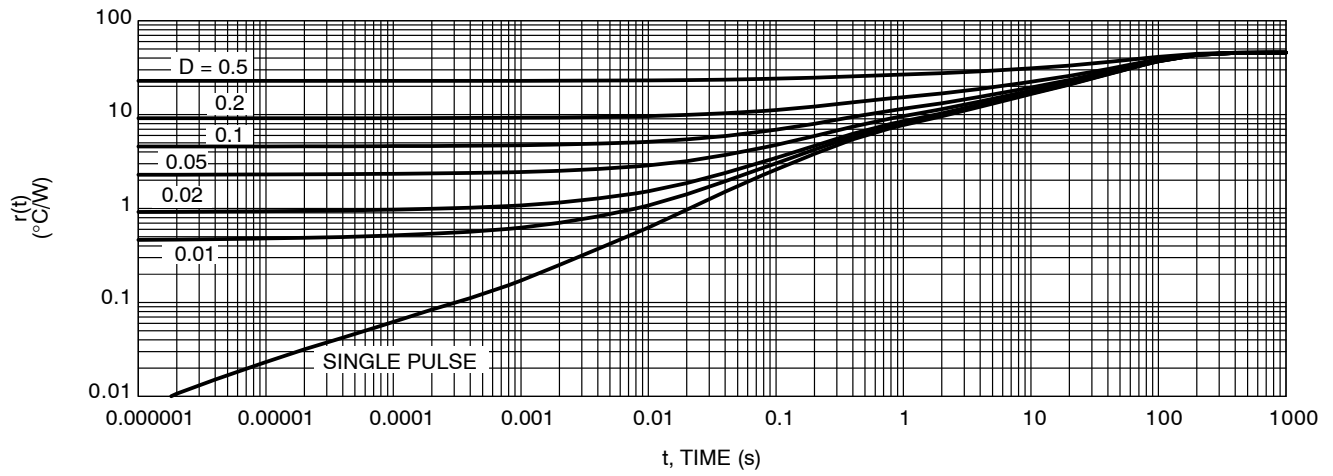


Figure 13. Thermal Response

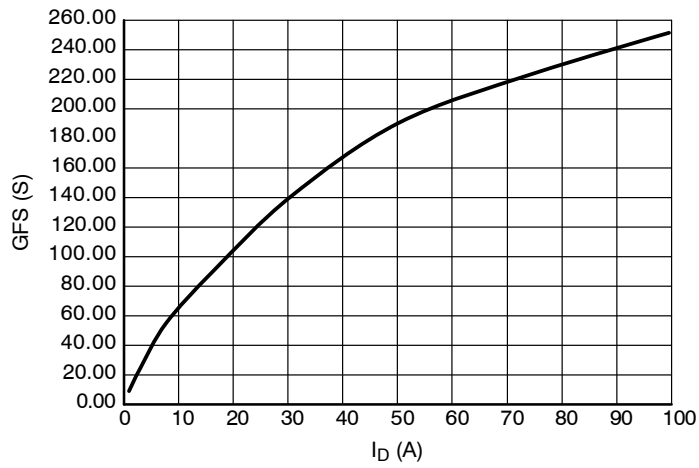


Figure 14. GFS vs. I_D

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PACKAGE DIMENSIONS

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE H

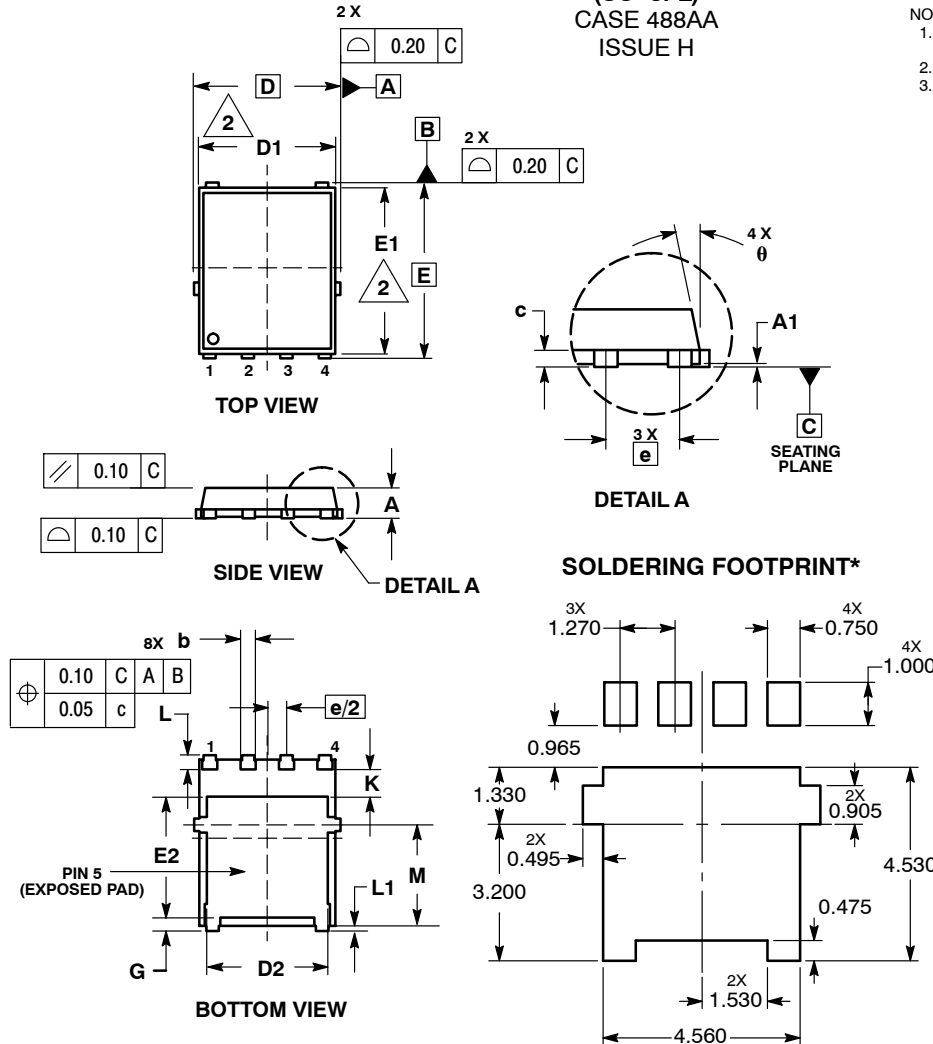
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

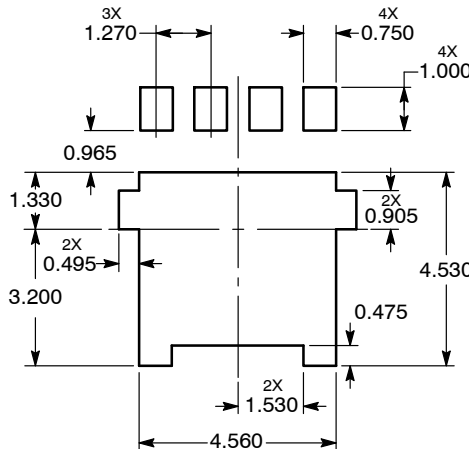
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.15 BSC		
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.15 BSC		
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.61	0.71
K	1.20	1.35	1.50
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
M	3.00	3.40	3.80
θ	0 °	---	12 °

STYLE 1:

- PIN 1. SOURCE
- SOURCE
- SOURCE
- GATE
- DRAIN



SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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